

Docket No.: 57454-329

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Masahiro SHIMIZU, et al.

Serial No.: 10/053,543

Filed: January 24, 2002



Response Under 37 CFR 1.116 - Expedited Procedure
Customer Number: 20277

Confirmation Number: 3990

Group Art Unit: 2814

Examiner: G. Peralta

For: INTEGRATED CIRCUIT HAVING A MEMORY CELL TRANSISTOR WITH A GATE OXIDE LAYER
WHICH IS THICKER THAN THE GATE OXIDE LAYER OF A PERIPHERAL CIRCUIT TRANSISTOR
(As Amended)

Box AF
Mail Stop AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Transmitted herewith is an Amendment in the above-identified application.

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☐

No additional fee is required.

Applicant is entitled to small entity status under 37 CFR 1.27

Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	1	20	0	\$18.00 =	\$0.00
Independent Claims	1	3	0	\$84.00 =	\$0.00
Multiple claims newly presented					\$0.00
Fee for extension of time					\$0.00
Total of Above Calculations					\$0.00

- ☐ Please charge my Deposit Account No. 500417 in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.
- ☒ The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

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PATENT

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PATENT

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: **RESPONSE UNDER 37 CFR 1.116**
: **EXPEDITED PROCEDURE**

: Customer Number: 20277
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For: INTEGRATED CIRCUIT HAVING A MEMORY CELL TRANSISTOR WITH A GATE OXIDE LAYER WHICH IS THICKER THAN THE GATE OXIDE LAYER OF A PERIPHERAL CIRCUIT TRANSISTOR (As Amended)

AMENDMENT UNDER 37 CFR §1.116

Mail Stop AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated May 7, 2003, pursuant to the provisions 37 C.F.R. §1.116.

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks/Arguments begin on page 3 of this paper.